36. (New) The method of claim 35, wherein the organosilicate layer contacts the polishing pad with a pressure within range of about 1 psi (pounds/square inch) to about 14 psi.

REMARKS

This is intended as a full and complete response to the Restriction Requirement dated February 26, 2003, having a shortened statutory period for response set to expire on March 26, 2003. Please reconsider the claims pending in the application for reasons discussed below.

Claims 1-29 are pending in the application and are subject to restriction and/or election requirement.

Restriction to one of the following inventions is required under 35 U.S.C. 121:

Claims 1-7, drawn to an abrasive composition, classified in class 51, subclass 293.

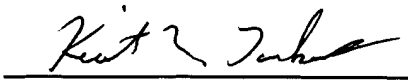
Claims 8-29, drawn to a method of planarizing a surface, classified in class 451, subclass 41.

Applicants have canceled claims 1-7 and added claims 30-36. Applicants submit that new claims 30-36 below to Group II. Applicants elect Group II, claims 8-36. Applicants submit that the changes made herein do not introduce new matter.

Applicants are submitting a proposed drawing amendment in a separate paper. The proposed corrections are also shown on the attached copy of the amended drawing. Applicants submit that the changes made therein do not introduce new matter.

Having addressed all issues set out in the office action, Applicants respectfully submit that the claims are in condition for allowance and respectfully request that the claims be allowed.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION:

Please replace paragraph [0047] with the following paragraph:

[0047] FIGS. 2a-2b illustrate schematic cross-sectional views of a substrate at different stages of an integrated circuit fabrication incorporating a planarization process. In general, the substrate 200 refers to any workpiece on which processing is performed, and [a] the term substrate structure [250] is used to denote the substrate 200 together with other material layers formed thereon. Depending on the specific stage of processing, the substrate 200 may correspond to a silicon wafer, or other material layer that has been formed on the silicon wafer.

Please replace paragraph [0048] with the following paragraph:

[0048] FIG. 2a, for example, illustrates a cross-sectional view of a substrate structure [250,] having conductive metal features 202 and an organosilicate layer 204, thereon. The organosilicate layer 204 is formed between and on top of each conductive metal feature 202. The organosilicate layer 202 is an intermetal dielectric for the conductive metal features 202.